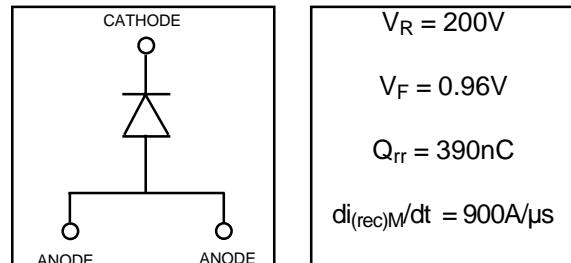


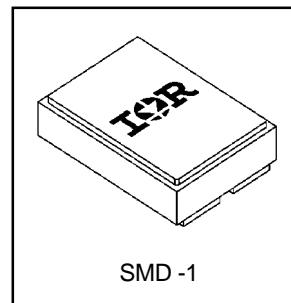
## Features

- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters
- Hermetic
- Surface Mount



## Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and  $di/dt$  simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



## Absolute Maximum Ratings (per Leg)

	Parameter	Max.	Units
$V_R$	D.C. Reverse Voltage	200	V
$I_F @ T_C = 100^\circ C$	Continuous Forward Current ①	100	A
$I_{FSM} @ T_C = 25^\circ C$	Single Pulse Forward Current ②	600	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	125	W
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	°C

## Thermal - Mechanical Characteristics

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case, Single Leg Conducting	—	1.0	°C/W
$W_t$	Weight	2.6	—	g

**Note:** ① D.C. = 50% rect. wave

② 1/2 sine wave, 60 Hz , P.W. = 8.33 ms

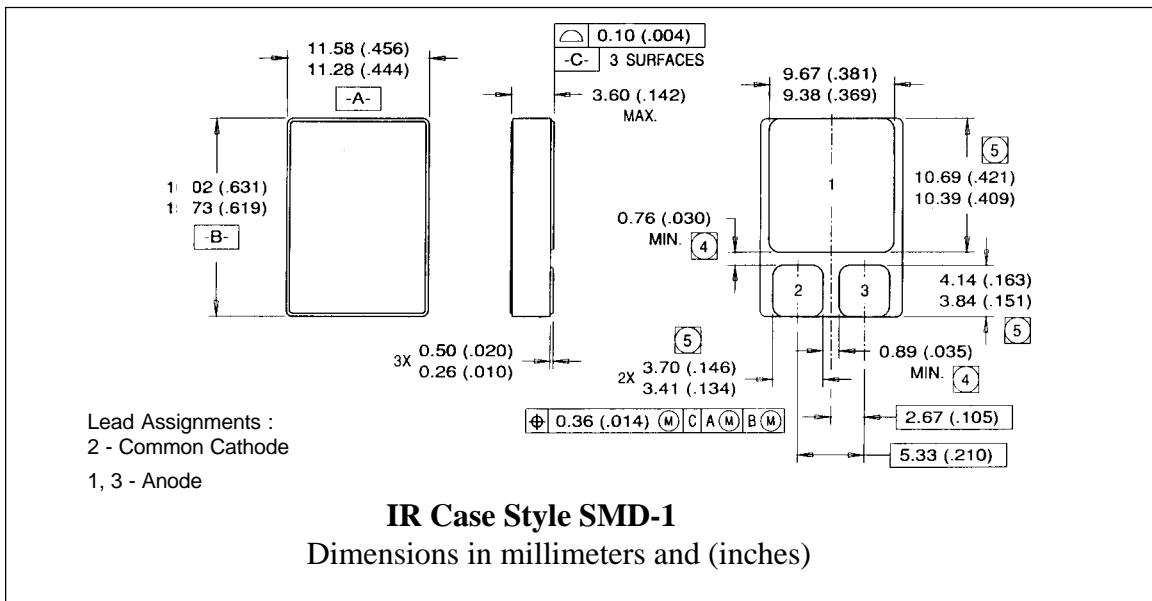
## Electrical Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

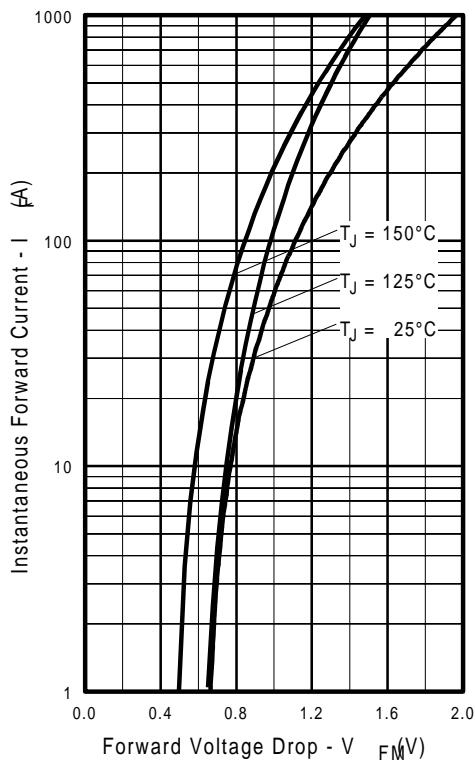
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{BR}$	Cathode Anode Breakdown Voltage	200	—	—	V	$I_R = 100\mu\text{A}$
$V_{FM}$	Max Forward Voltage	—	—	0.96	V	$I_F = 50\text{A}$
		—	—	1.11		$I_F = 100\text{A}$
		—	—	0.84		See Fig. 1
		—	—	—		$I_F = 50\text{A}, T_J = 125^\circ\text{C}$
$I_{RM}$	Max Reverse Leakage Current	—	—	10	$\mu\text{A}$	$V_R = V_R$ Rated
		—	—	1.0	$\text{mA}$	$T_J = 125^\circ\text{C}, V_R = 160\text{V}$
$C_T$	Junction Capacitance	—	170	253	$\text{pF}$	$V_R = 200\text{V}$
$L_S$	Series Inductance	—	2.8	—	$\text{nH}$	Measured from center of bond pad to end of anode bonding wire

## Dynamic Recovery Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

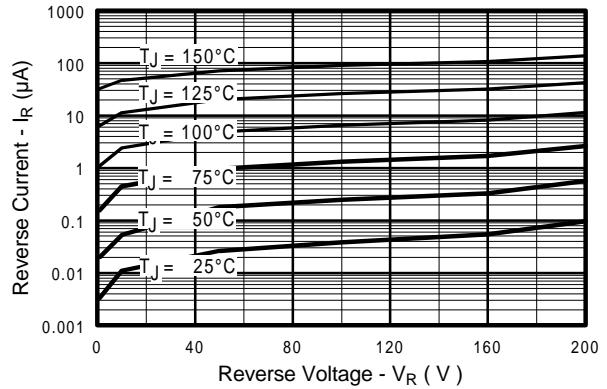
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{rr1}$	Reverse Recovery Time	—	62	93	ns	$T_J = 25^\circ\text{C}$
$t_{rr2}$		—	98	150		$T_J = 125^\circ\text{C}$
$I_{RRM1}$	Peak Recovery Current	—	10	15	A	$T_J = 25^\circ\text{C}$
$I_{RRM2}$		—	14	21		$T_J = 125^\circ\text{C}$
$Q_{rr1}$	Reverse Recovery Charge	—	260	390	nC	$T_J = 25^\circ\text{C}$
$Q_{rr2}$		—	640	960		$T_J = 125^\circ\text{C}$
$dI_{(rec)M}/dt_1$	Peak Rate of Fall of Recovery Current	—	600	900	$A/\mu\text{s}$	$T_J = 25^\circ\text{C}$
$dI_{(rec)M}/dt_2$		—	980	1500		$T_J = 125^\circ\text{C}$
	During $t_b$	—	—	—		See Fig. 8

## Case Outline and Dimensions — SMD-1

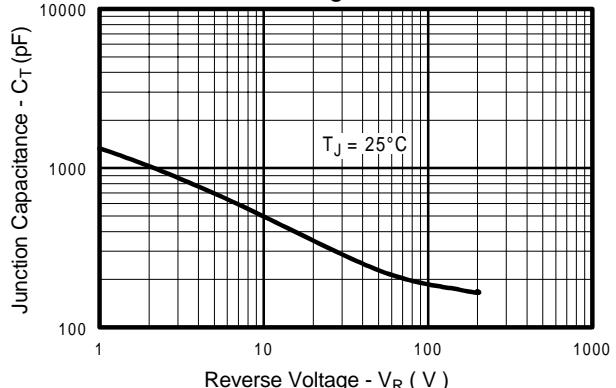




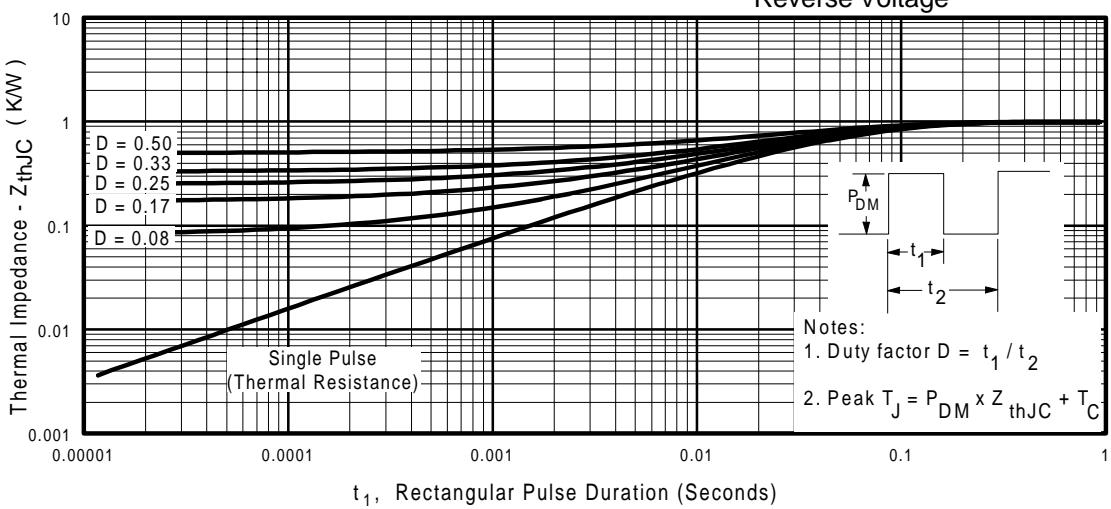
**Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current**



**Fig. 2 - Typical Reverse Current vs. Reverse Voltage**



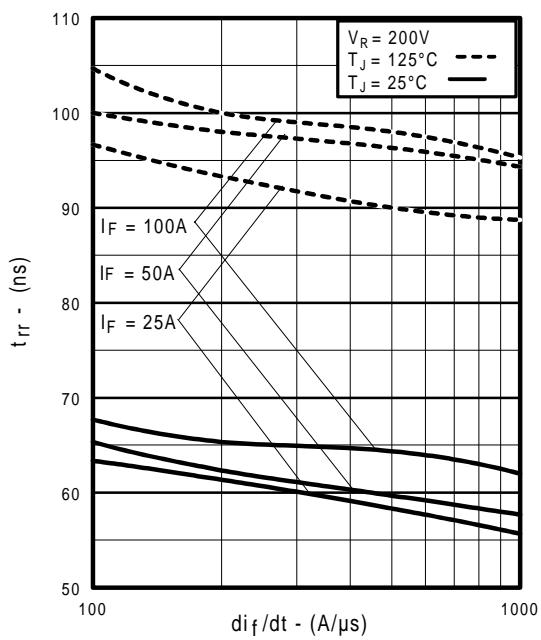
**Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage**



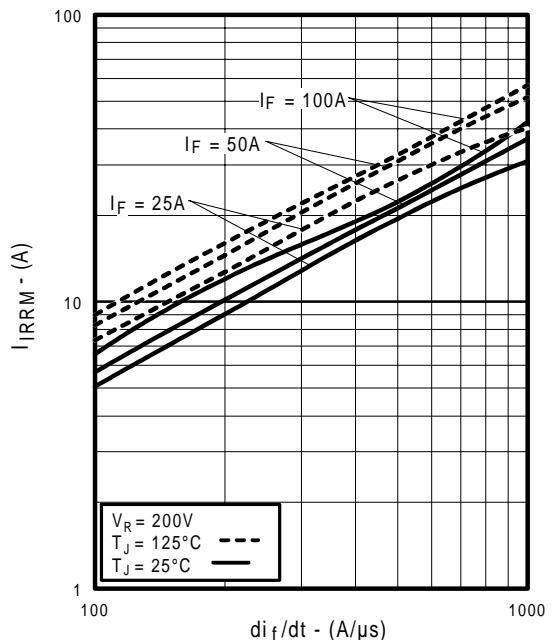
**Fig. 4 - Maximum Thermal Impedance  $Z_{thjc}$  Characteristics**

# HFA50HF20

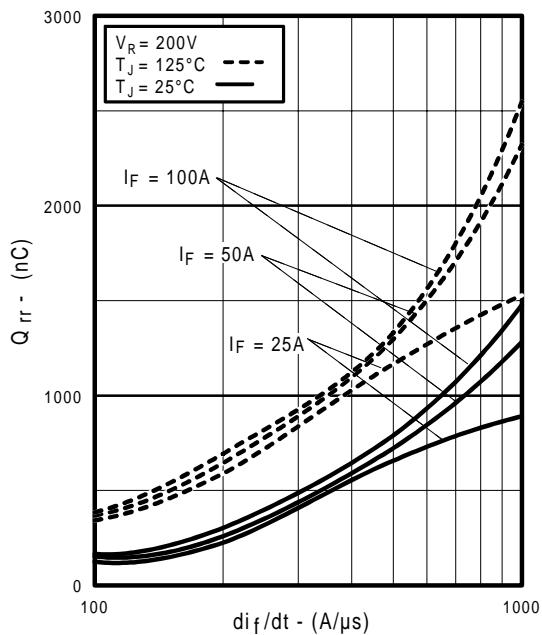
International  
**IR** Rectifier



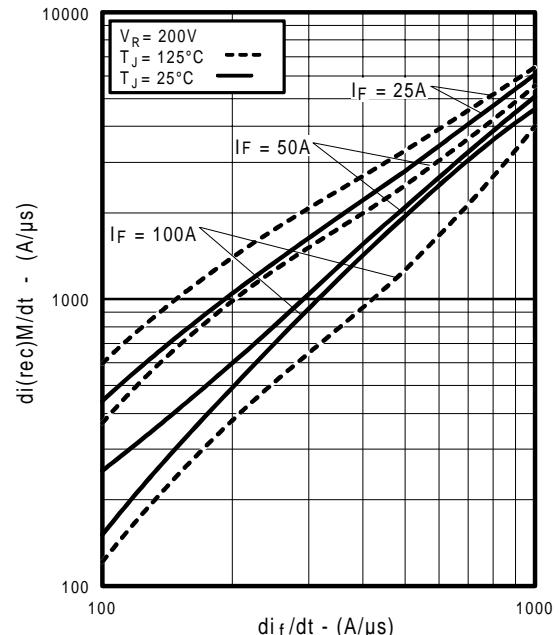
**Fig. 5** - Typical Reverse Recovery vs.  $di/dt$ ,



**Fig. 6** - Typical Recovery Current vs.  $di/dt$ ,

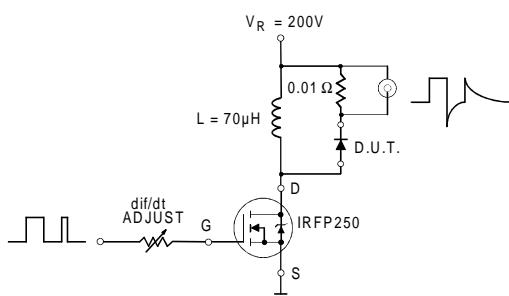


**Fig. 7** - Typical Stored Charge vs.  $di/dt$

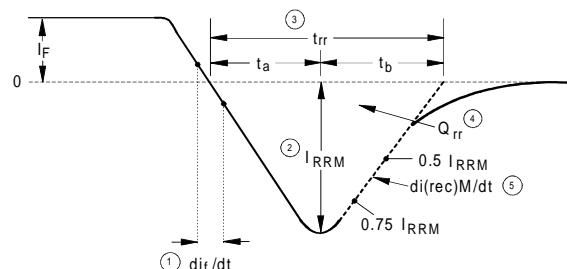


**Fig. 8** - Typical  $di_{(rec)}/dt$  vs.  $di/dt$

REVERSE RECOVERY CIRCUIT



**Fig. 9 - Reverse Recovery Parameter Test Circuit**



1.  $di/dt$  - Rate of change of current through zero crossing

2.  $I_{RRM}$  - Peak reverse recovery current

3.  $t_{rr}$  - Reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75  $I_{RRM}$  and 0.50  $I_{RRM}$  extrapolated to zero current

4.  $Q_{rr}$  - Area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

5.  $di_{(rec)M}/dt$  - Peak rate of change of current during  $t_b$  portion of  $t_{rr}$

**Fig. 10 - Reverse Recovery Waveform and Definitions**

International  
**IR** Rectifier

**WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

**IR GREAT BRITAIN:** Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

**IR CANADA:** 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

**IR FAR EAST:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

**IR SOUTHEAST ASIA:** 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 221 8371

**IR TAIWAN:** 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

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